

## N-Channel Power MOSFET

600V, 24A, 150mΩ

### FEATURES

- Super-Junction technology
- High performance, small  $R_{DS(on)} * Q_g$  figure of merit (FOM)
- High ruggedness performance
- 100% UIS and  $R_g$  tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

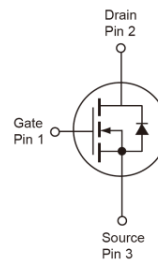
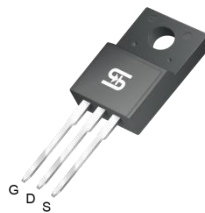
KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
$V_{DS}$	600	V
$R_{DS(on)}$ (max)	150	mΩ
$Q_g$	43	nC

### APPLICATIONS

- PFC Stage
- Power Supply
- AC/DC LED Lighting



ITO-220S



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current <sup>(Note 1)</sup>	$I_D$	$T_C = 25^\circ\text{C}$	24
		$T_C = 100^\circ\text{C}$	15
Pulsed Drain Current <sup>(Note 2)</sup>	$I_{DM}$	72	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	$P_D$	62.5	W
Single Pulse Avalanche Energy <sup>(Note 3)</sup>	$E_{AS}$	441	mJ
Single Pulse Avalanche Current <sup>(Note 3)</sup>	$I_{AS}$	4.2	A
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	2	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	62	$^\circ\text{C/W}$

**Thermal Performance Note:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
<b>Static</b> (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	$BV_{DSS}$	600	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2	3.2	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	$I_{DSS}$	--	--	1	$\mu A$
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 4.3A$	$R_{DS(on)}$	--	124	150	m $\Omega$
<b>Dynamic</b> (Note 5)						
Total Gate Charge	$V_{DS} = 480V, I_D = 13A,$ $V_{GS} = 10V$	$Q_g$	--	43	--	nC
Gate-Source Charge		$Q_{gs}$	--	10	--	
Gate-Drain Charge		$Q_{gd}$	--	17	--	
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$ $f = 1.0MHz$	$C_{iss}$	--	1765	--	pF
Output Capacitance		$C_{oss}$	--	84	--	
Reverse Transfer Capacitance		$C_{rss}$	--	11	--	
Gate Resistance	$f = 1.0MHz$	$R_g$	--	3	6	$\Omega$
<b>Switching</b> (Note 6)						
Turn-On Delay Time	$V_{DD} = 300V, R_{GEN} = 5\Omega,$ $I_D = 6.5A, V_{GS} = 10V$	$t_{d(on)}$	--	14	--	ns
Turn-On Rise Time		$t_r$	--	21	--	
Turn-Off Delay Time		$t_{d(off)}$	--	52	--	
Turn-Off Fall Time		$t_f$	--	21	--	
<b>Source-Drain Diode</b> (Note 4)						
Body-Diode Continuous Forward Current		$I_S$	--	--	24	A
Body-Diode Pulsed Current		$I_{SM}$	--	--	72	A
Forward Voltage	$I_S = 13A, V_{GS} = 0V$	$V_{SD}$	--	--	1.4	V
Reverse Recovery Time	$I_S = 6.5A$ $di_f/dt = 100A/\mu s$	$t_{rr}$	--	241	--	ns
Reverse Recovery Charge		$Q_{rr}$	--	2.4	--	$\mu C$

**Notes:**

1. Current limited by package.
2. Pulse width limited by the maximum junction temperature.
3.  $L = 50mH, I_{AS} = 4.2A, V_{DD} = 50V, R_G = 25\Omega,$  Starting  $T_J = 25^\circ C$
4. Pulse test:  $PW \leq 300\mu s,$  duty cycle  $\leq 2\%$ .
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

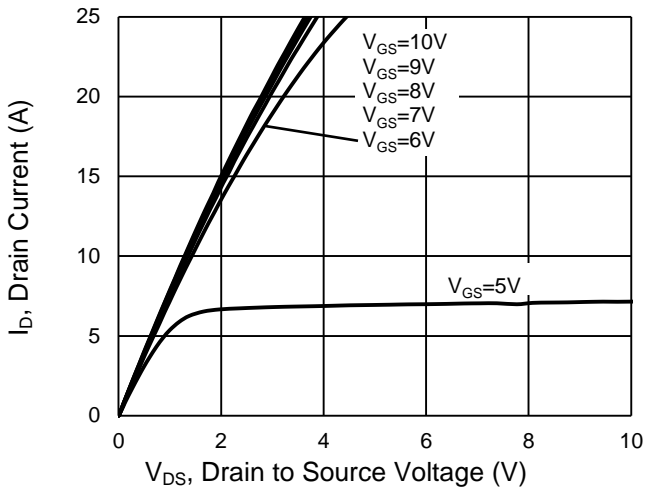
**ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM60NB150CF C0G	ITO-220S	50pcs / Tube

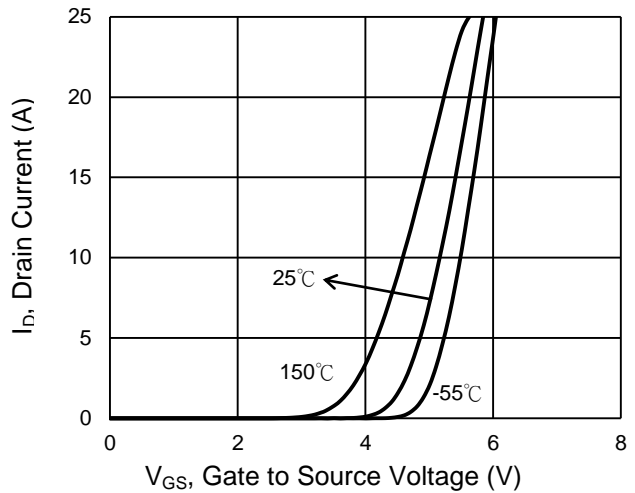
**CHARACTERISTICS CURVES**

( $T_c = 25^\circ\text{C}$  unless otherwise noted)

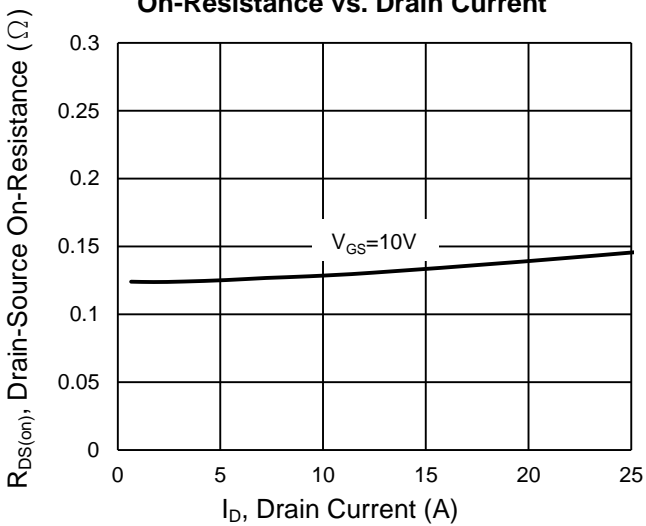
**Output Characteristics**



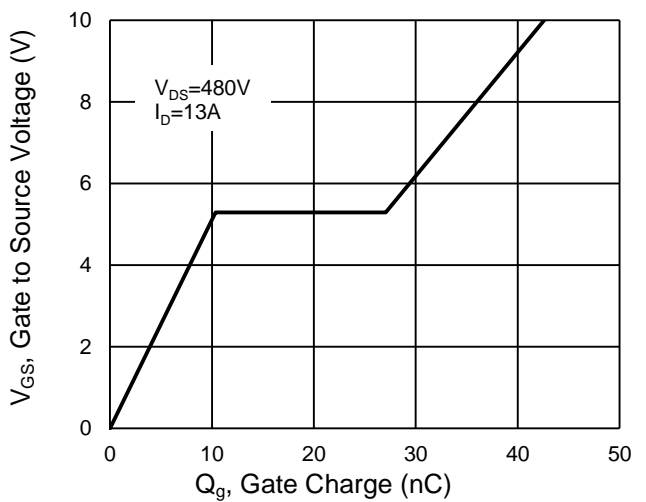
**Transfer Characteristics**



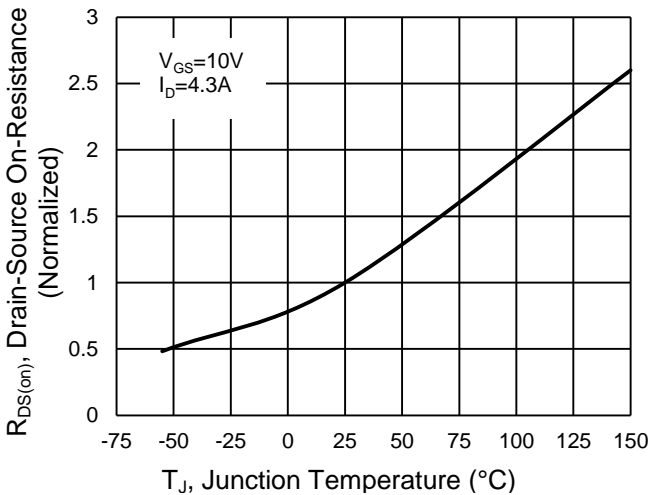
**On-Resistance vs. Drain Current**



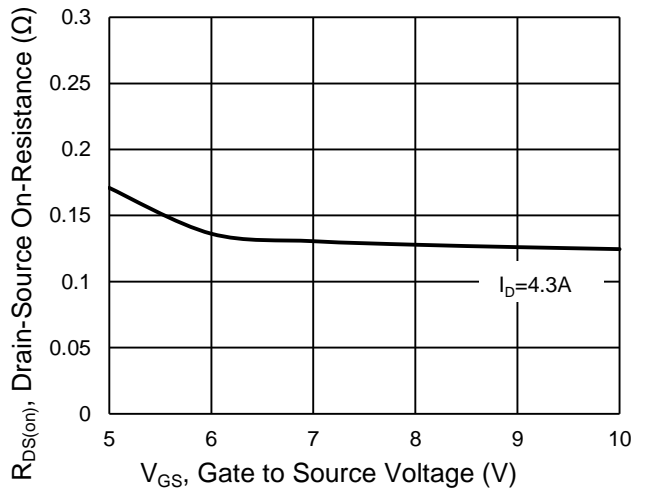
**Gate-Source Voltage vs. Gate Charge**



**On-Resistance vs. Junction Temperature**



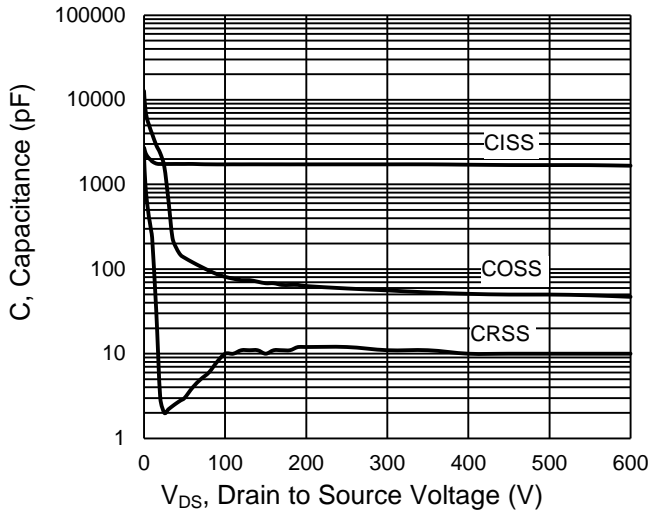
**On-Resistance vs. Gate-Source Voltage**



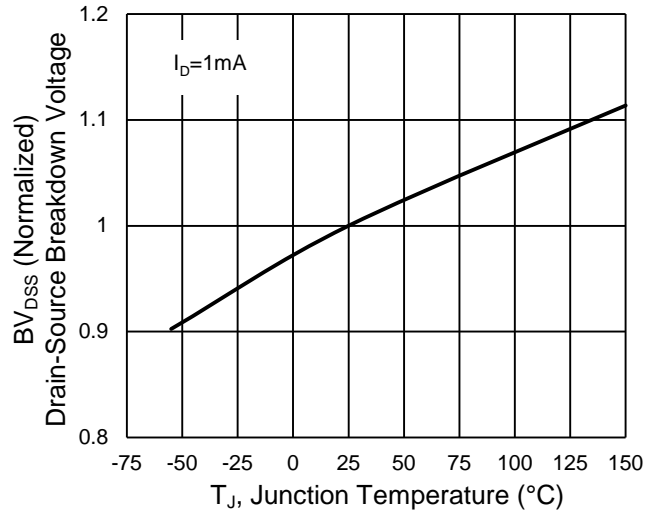
**CHARACTERISTICS CURVES**

( $T_C = 25^\circ\text{C}$  unless otherwise noted)

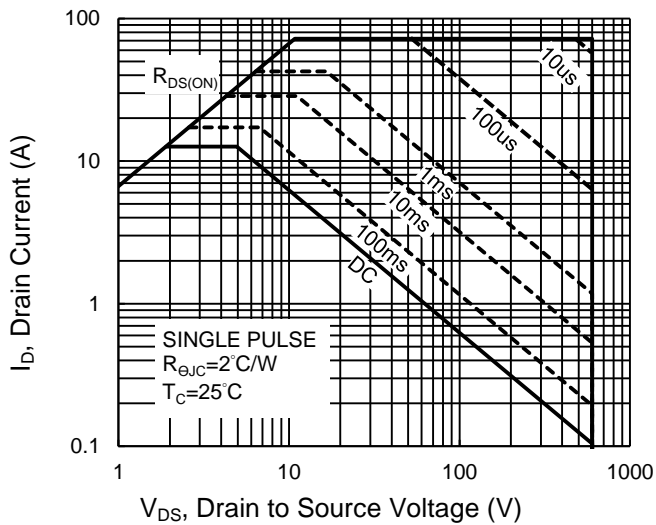
**Capacitance vs. Drain-Source Voltage**



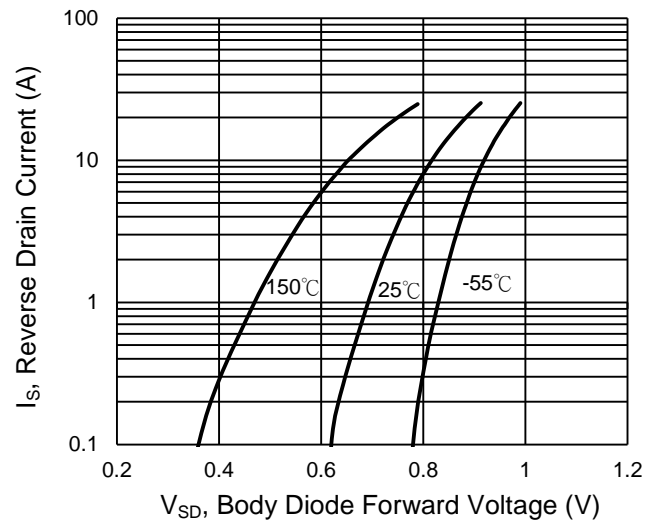
**$BV_{DSS}$  vs. Junction Temperature**



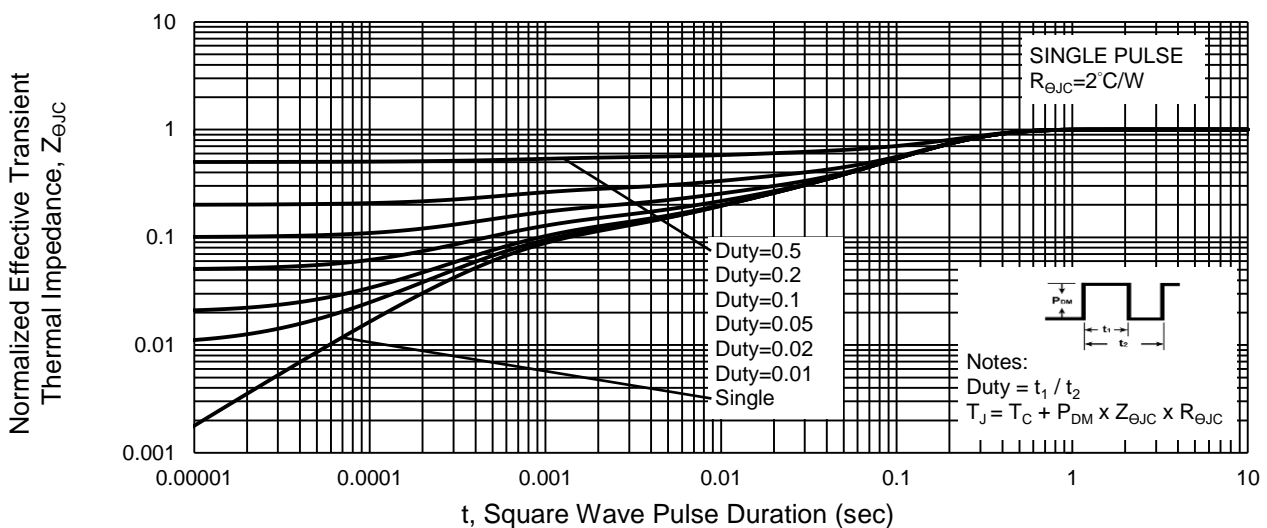
**Maximum Safe Operating Area, Junction-to-Case**



**Source-Drain Diode Forward Current vs. Voltage**

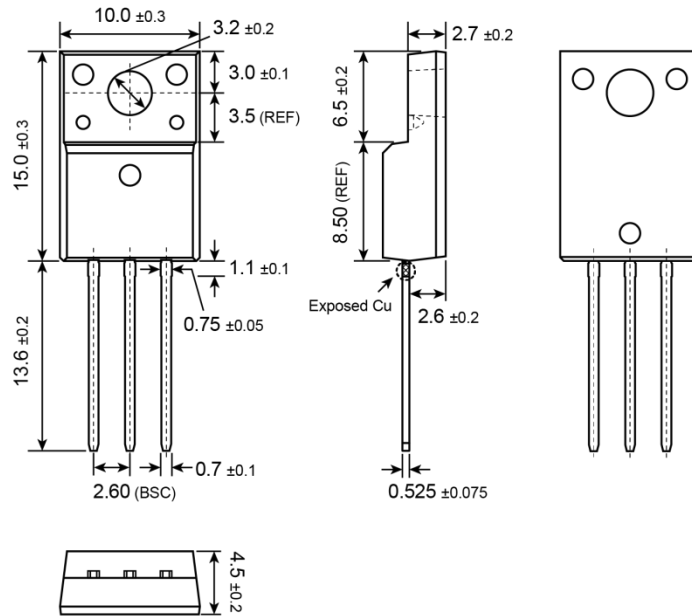


**Normalized Thermal Transient Impedance, Junction-to-Case**

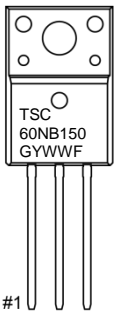


**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)

**ITO-220S**



**MARKING DIAGRAM**



- G** = Halogen Free
- Y** = Year Code
- WW** = Week Code (01~52)
- F** = Factory Code

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